

MOSFETs Silicon N-channel MOS (U-MOSIX-H)

# TPWR8004PL

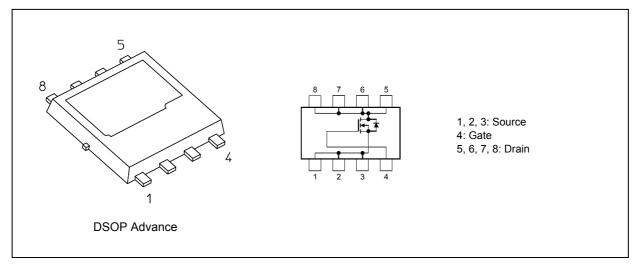
### 1. Applications

- · High-Efficiency DC-DC Converters
- Switching Voltage Regulators
- · Motor Drivers

### 2. Features

- (1) High-speed switching
- (2) Small gate charge:  $Q_{SW} = 23 \text{ nC (typ.)}$
- (3) Small output charge:  $Q_{oss} = 85.4 \text{ nC (typ.)}$
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 0.65 \text{ m}\Omega$  (typ.) ( $V_{GS} = 10 \text{ V}$ )
- (5) Low leakage current:  $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 40 \text{ V)}$
- (6) Enhancement mode:  $V_{th} = 1.4 \text{ to } 2.4 \text{ V (V}_{DS} = 10 \text{ V}, I_D = 1.0 \text{ mA)}$

### 3. Packaging and Internal Circuit





### 4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

| Characteris                    | stics                                      |                    | Symbol           | Rating     | Unit |
|--------------------------------|--|--------------------|------------------|------------|------|
| Drain-source voltage           |  |                    | $V_{DSS}$        | 40         | V    |
| Gate-source voltage            |  |                    | $V_{GSS}$        | ±20        |      |
| Drain current (DC)             | (T <sub>c</sub> = 25 °C)<br>(Bottom drain) | (Note 1), (Note 2) | I <sub>D</sub>   | 150        | Α    |
| Drain current (DC)             | (Silicon limit)                            | (Note 1), (Note 2) | I <sub>D</sub>   | 340        | Α    |
| Drain current (pulsed)         | (t = 100 μs)                               | (Note 1)           | I <sub>DP</sub>  | 500        | Α    |
| Power dissipation              | (T <sub>c</sub> = 25 °C)<br>(Bottom drain) |                    | $P_D$            | 170        | W    |
| Power dissipation              |  | (Note 3)           | P <sub>D</sub>   | 3.0        | W    |
| Power dissipation              |  | (Note 4)           | P <sub>D</sub>   | 1.0        | W    |
| Single-pulse avalanche energy  |  | (Note 5)           | E <sub>AS</sub>  | 336        | mJ   |
| Single-pulse avalanche current |  | (Note 5)           | I <sub>AS</sub>  | 120        | Α    |
| Channel temperature            |  |                    | T <sub>ch</sub>  | 175        | °C   |
| Storage temperature            |  |                    | T <sub>stg</sub> | -55 to 175 | °C   |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

### 5. Thermal Characteristics

| Characteristic                        | Symbol                                   | Max      | Unit                  |      |      |
|---------------------------------------|--|----------|-----------------------|------|------|
| Channel-to-case thermal resistance    | Bottom drain<br>(T <sub>c</sub> = 25 °C) |          | R <sub>th(ch-c)</sub> | 0.88 | °C/W |
| Channel-to-case thermal resistance    | Top source<br>(T <sub>c</sub> = 25 °C)   |          | R <sub>th(ch-c)</sub> | 0.93 | °C/W |
| Channel-to-ambient thermal resistance | (T <sub>a</sub> = 25 °C)                 | (Note 3) | R <sub>th(ch-a)</sub> | 50   | °C/W |
| Channel-to-ambient thermal resistance | (T <sub>a</sub> = 25 °C)                 | (Note 4) | R <sub>th(ch-a)</sub> | 142  | °C/W |

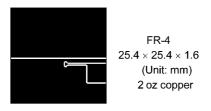
Note 1: Ensure that the channel temperature does not exceed 175 °C.

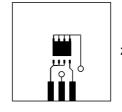
Note 2: Limited by package limit. Silicon chip capability is 340 A. ( $T_c = 25$  °C)(Bottom drain)

Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5:  $V_{DD}$  = 32 V,  $T_{ch}$  = 25 °C (initial), L = 18  $\mu H$ ,  $I_{AS}$  = 120 A





FR-4 25.4 × 25.4 × 1.6 (Unit: mm) 2 oz copper

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



### 6. Electrical Characteristics

# 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                | Symbol               | Test Condition                                    | Min | Тур. | Max  | Unit |
|--------------------------------|----------------------|---|-----|------|------|------|
| Gate leakage current           | I <sub>GSS</sub>     | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | _   | _    | ±0.1 | μΑ   |
| Drain cut-off current          | I <sub>DSS</sub>     | V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V     | _   | _    | 10   |      |
| Drain-source breakdown voltage | V <sub>(BR)DSS</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V     | 40  | _    |      | V    |
|                                | V <sub>(BR)DSX</sub> | $I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$     | 25  | _    |      |      |
| Gate threshold voltage         | $V_{th}$             | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.0 mA   | 1.4 | _    | 2.4  |      |
| Drain-source on-resistance     | R <sub>DS(ON)</sub>  | $V_{GS} = 4.5 \text{ V}, I_D = 50 \text{ A}$      | _   | 0.95 | 1.35 | mΩ   |
|                                |                      | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 50 A     | _   | 0.65 | 0.80 |      |

# 6.2. Dynamic Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                | Symbol           | Test Condition   | Min | Тур. | Max  | Unit |
|--------------------------------|------------------|--|-----|------|------|------|
| Input capacitance              | C <sub>iss</sub> | V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V, f = 1 MHz | _   | 7370 | 9600 | pF   |
| Reverse transfer capacitance   | C <sub>rss</sub> |  | _   | 58   | _    |      |
| Output capacitance             | C <sub>oss</sub> |  | _   | 1930 | _    |      |
| Gate resistance                | r <sub>g</sub>   | _  | _   | 0.6  | 1.1  | Ω    |
| Switching time (rise time)     | t <sub>r</sub>   | See Fig. 6.2.1   | _   | 13   | _    | ns   |
| Switching time (turn-on time)  | t <sub>on</sub>  |  | _   | 26   | _    |      |
| Switching time (fall time)     | t <sub>f</sub>   |  | _   | 14   | _    |      |
| Switching time (turn-off time) | t <sub>off</sub> |  | _   | 63   | _    |      |

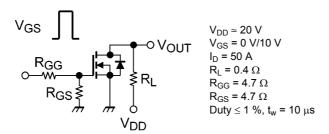


Fig. 6.2.1 Switching Time Test Circuit

# 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                     | Symbol           | Test Condition  | Min | Тур. | Max | Unit |
|-------------------------------------|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus | $Q_g$            | $V_{DD} \approx 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 50 \text{ A}$  |     | 103  | 1   | nC   |
| gate-drain)                         |                  | $V_{DD} \approx 20 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 50 \text{ A}$ |     | 49   |     |      |
| Gate-source charge 1                | Q <sub>gs1</sub> | $V_{DD} \approx 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 50 \text{ A}$  |     | 25   |     |      |
| Gate-drain charge                   | $Q_{gd}$         |   |     | 12.4 |     |      |
| Gate switch charge                  | $Q_{\text{SW}}$  |   | _   | 23   | _   |      |
| Output charge                       | Q <sub>oss</sub> | V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V                             | _   | 85.4 | _   |      |

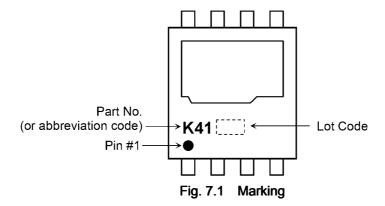
# 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                         | Symbol                        | Test Condition   | Min | Тур. | Max  | Unit |
|---|-------------------------------|--|-----|------|------|------|
| Reverse drain current (pulsed) (Note 6) | I <sub>DRP</sub> (t = 100 μs) | _  |     | -    | 500  | Α    |
| Diode forward voltage                   | V <sub>DSF</sub>              | I <sub>DR</sub> = 150 A, V <sub>GS</sub> = 0 V                     |     | _    | -1.2 | V    |
| Reverse recovery time                   |                               | V <sub>R</sub> = 20 V, I <sub>DR</sub> = 37.5 A, V <sub>GS</sub> = | _   | 58   | _    | ns   |
| Reverse recovery charge                 | Q <sub>rr</sub>               | 0 V, -dl <sub>DR</sub> /dt = 100 A/μs                              | _   | 70   | _    | nC   |

Note 6: Ensure that the channel temperature does not exceed 175 °C.



# 7. Marking





### 8. Characteristics Curves (Note)

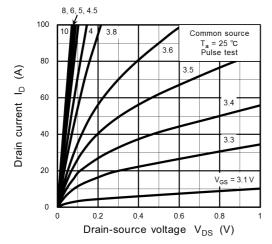


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>

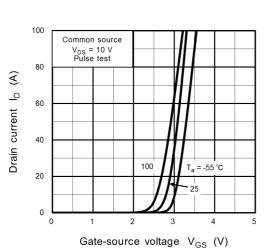


Fig. 8.3 I<sub>D</sub> - V<sub>GS</sub>

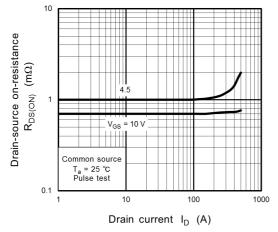


Fig. 8.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

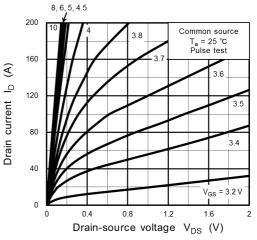
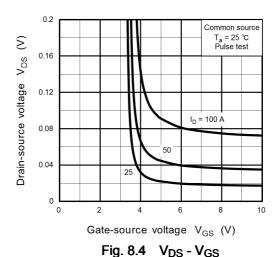


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>



 $\begin{array}{c} \text{(V)} \\ \text{(V)$ 

Fig. 8.6  $I_{DR}$  -  $V_{DS}$ 



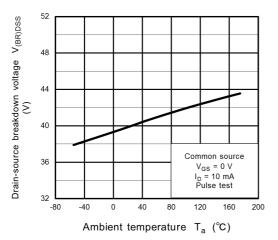


Fig. 8.7 V<sub>(BR)DSS</sub> - T<sub>a</sub>

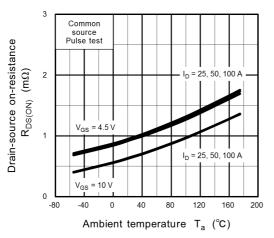


Fig. 8.9 R<sub>DS(ON)</sub> - T<sub>a</sub>

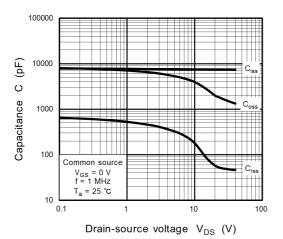


Fig. 8.11 Capacitance - V<sub>DS</sub>

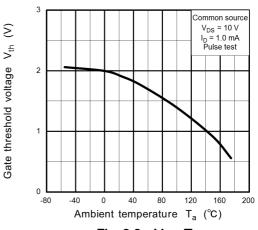


Fig. 8.8 V<sub>th</sub> - T<sub>a</sub>

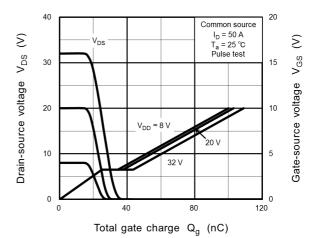


Fig. 8.10 Dynamic Input/Output Characteristics

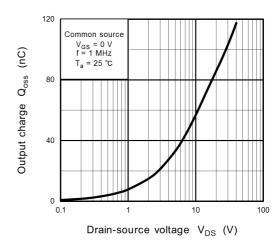


Fig. 8.12 Qoss - VDS



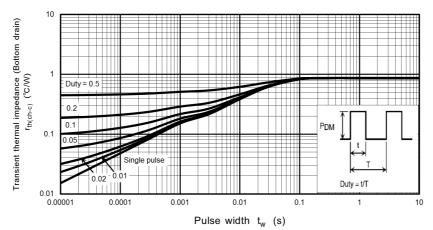


Fig. 8.13 r<sub>th</sub> - t<sub>w</sub> (Bottom drain) (Guaranteed Maximum)

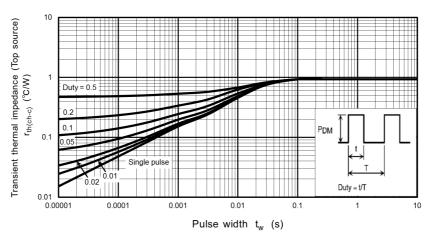


Fig. 8.14 r<sub>th</sub> - t<sub>w</sub> (Top source) (Guaranteed Maximum)

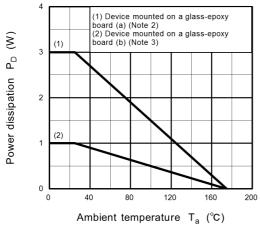


Fig. 8.15 P<sub>D</sub> - T<sub>a</sub> (Guaranteed Maximum)

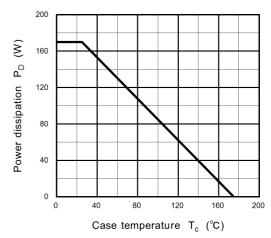


Fig. 8.16 P<sub>D</sub> - T<sub>c</sub> (Bottom drain) (Guaranteed Maximum)



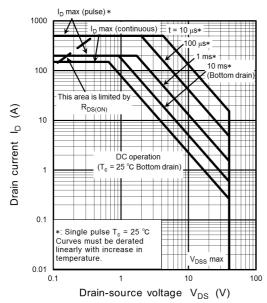


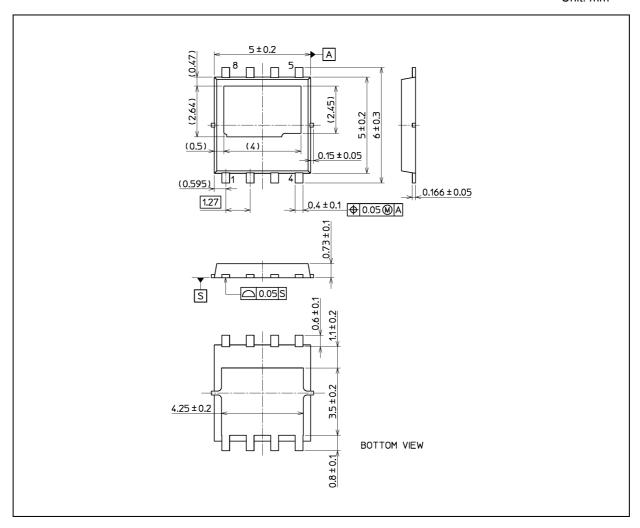
Fig. 8.17 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



# **Package Dimensions**

Unit: mm



Weight: 0.104 g (typ.)

| Package Name(s)        |
|------------------------|
| TOSHIBA: 2-5S1A        |
| Nickname: DSOP Advance |



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